



MJD32CQ

100V PNP HIGH VOLTAGE TRANSISTOR IN TO252

Description

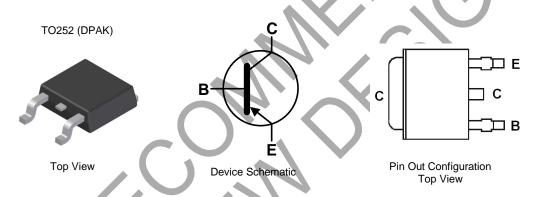
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

- BV_{CEO} > -100V
- I_C = -3A high Continuous Collector Current
- I_{CM} = -5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary NPN Type: MJD31CQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.34 grams (Approximate)



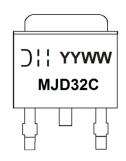
Ordering Information (Notes 4 & 5

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MJD32CQ-13	Automotive	MJD32C	13	16	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



MJD32C = Product Type Marking Code

| Manufacturers' code marking

| YYWW = Date Code Marking
| YY = Last Digit of Year (ex: 16 = 2016)

| WW = Week Code (01 - 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	lc	-3	А
Peak Pulse Collector Current	I _{CM}	-5	А
Continuous Base Current	lΒ	-1	А
Power Dissipation	P_{D}	15	W

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

T				
Characteristic	Symbol	Value	Unit	
	(Note 6)		3.9	
Power Dissipation	(Note 7)	P _D	2.1	W
	(Note 8)		1.6	
	(Note 6)		32	
Thermal Resistance, Junction to Ambient Air	(Note 7)	Reja	59	°C/W
	(Note 8)		80	C/VV
Thermal Resistance, Junction to Leads	(Note 9)	R _{BJL}	8.4	
Operating and Storage Temperature Range		TJ, T _{STG}	-55 to +150	°C

ESD Ratings (Note 10)

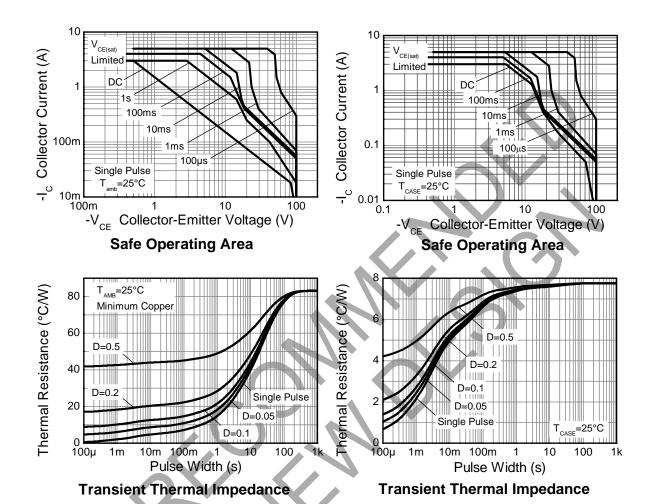
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:

- 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as note (6), except mounted on 25mm x 25mm 1oz copper.
 8. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

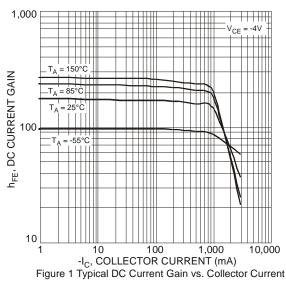
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100			V	$I_C = -30 \text{mA}, I_B = 0$
Collector Cut-off Current	ICEO	_	_	-1	μΑ	$V_{CB} = -60V, I_B = 0$
Collector Cut-off Current	I _{CES}	_	_	-1	μΑ	$V_{CE} = -100V, V_{EB} = 0$
Emitter Cut-off Current	I _{EBO}	_	_	-1	μΑ	$V_{EB} = -5V, I_{C} = 0$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	_	-1.2	V	$I_C = -3.0A$, $I_B = -375mA$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	_	-1.8	V	$I_C = -3A$, $V_{CE} = -4V$
DC Current Gain (Note 11)	h _{FE}	25	_	_		$V_{CE} = -4V, I_{C} = -1A$
De durioni dam (Noto 11)	· · · F E	10		50		$V_{CE} = -4V, I_{C} = -3A$
Current Signal Current Gain	H_{fe}	20	_	_	-/	$V_{CE} = -10V$, $I_{C} = -0.5A$, $f = 1KHz$
Current Gain-Bandwidth Product	f⊤	3.0	_	_	MHz	$I_C = -500 \text{mA}, V_{CE} = -10 \text{V}, f = 1 \text{MHz}$

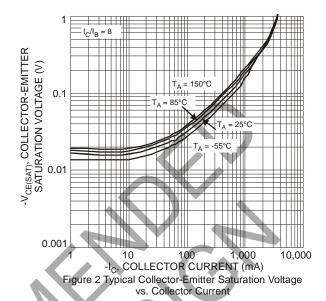
Note: 11. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

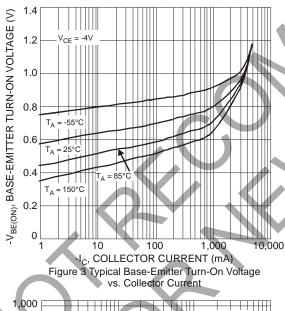


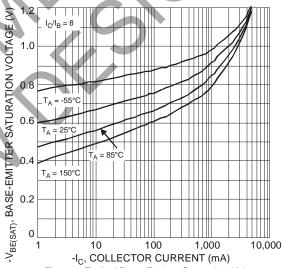


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









1,000 (AB) 100 100 100 V_R, REVERSE VOLTAGE (V)

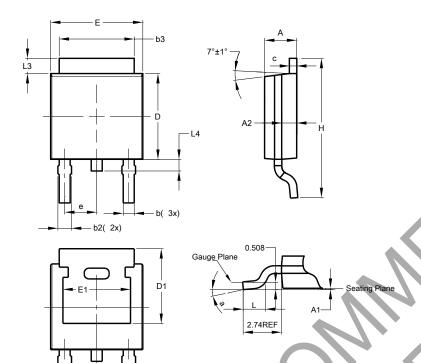
Figure 5 Typical Capacitance Characteristics

Figure 4 Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

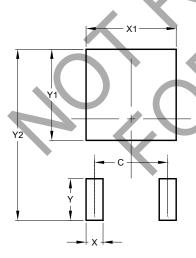
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
C	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	-)'	
D1 e	5.21	-	2.286	
-	5.21 - 6.45	6.70	2.286 6.58	
е	-	- - 6.70 -		
e E	6.45	6.70 - 10.41		
e E E1	- 6.45 4.32	/ -	6.58	
e E E1 H	6.45 4.32 9.40	- 10.41	6.58 - 9.91	
e E E1 H	6.45 4.32 9.40 1.40	- 10.41 1.78	6.58 - 9.91 1.59	
e E E1 H L	6.45 4.32 9.40 1.40 0.88	10.41 1.78 1.27	6.58 - 9.91 1.59 1.08	

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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